Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

CLAIMS LISTING (all of pending claims 1-20)

Claim 1 (*Currently Amended*): A method of forming sidewall dielectric on an ONO-type memory cell stack where at least one sidewall of the ONO-type memory cell stack includes at least three ~~a plurality of~~ exposed material layers with at least two of the exposed material layers being respectively composed of different materials, the method comprising:

(a) subjecting the at least one sidewall to a dry ISSG process (In-Situ Steam Generation) where the dry ISSG process comprises:

(a.1) flowing molecular oxygen (O_2) towards the stack; and

(a.2) flowing molecular hydrogen (H_2) towards the stack, where the volumetric flow ratio of the H_2 to the O_2 is less than about 0.2.

Claim 2 (*Original*): The sidewall dielectric forming method of Claim 1 wherein:

(a.2a) said volumetric flow ratio of H_2/O_2 is less than about 0.1.

Claim 3 (*Original*): The sidewall dielectric forming method of Claim 1 wherein:

(a.2a) said volumetric flow ratio of H_2/O_2 is equal to, or less than, about 0.02.

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Claim 4 (*Currently Amended*): The sidewall dielectric forming method of Claim 3 ~~1~~ and further comprising:

(b) rapidly heating the flowing oxygen (O_2) and flowing hydrogen (H_2) to a temperature in the range of about 850°C to about 1050°C as they flow towards said at least one sidewall.

Claim 5 (*Currently Amended*): The sidewall dielectric forming method of Claim 3 ~~1~~ and further comprising:

(b) continuing the subjecting of the at least one sidewall to the dry ISSG process for a duration selected from the range of about 20 seconds to about 300 seconds.

Claim 6 (*Currently Amended*): The sidewall dielectric forming method of Claim 1 and further comprising:

(a.1a) ~~setting or~~ varying the O_2 flow rate over the range of about 3slm to about 10slm (ten standard liters per minute).

Claim 7 (*Currently Amended*): The sidewall dielectric forming method of Claim 1 and further comprising:

(a.2a) ~~setting or~~ varying the H_2 flow rate over the range of about 0.1slm to about 1slm.

Claim 8 (*Currently Amended*): The sidewall dielectric forming method of Claim 3 ~~1~~ and further comprising:

(b) establishing a chamber pressure for the flowing oxygen (O_2) and flowing hydrogen (H_2) in the range of about 5 Torr to about 50 Torr.

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Claim 9 (*Currently Amended*): The sidewall dielectric forming method of Claim 1 and further wherein:

(b) said at least three ~~a plurality of~~ exposed material layers of the ONO-type memory cell stack includes:

(b.1) a first silicon nitride layer;

(b.2) a first silicon layer; and

(b.3) a first silicon oxide layer.

Claim 10 (*Currently Amended*): The sidewall dielectric forming method of Claim 9 and further wherein said at least three ~~a plurality of~~ exposed material layers of the ONO-type memory cell stack includes:

(b.4) a second silicon layer;

(b.5) a second silicon oxide layer;

(b.6) a tunnel dielectric layer;

(b.7) wherein the first silicon nitride layer is interposed between the first and second silicon oxide layers; and

(b.8) wherein the combination of the first and second silicon oxide layers and the first silicon nitride layer is interposed between the first and second silicon layers.

Claim 11 (*Currently Amended*): The sidewall dielectric forming method of Claim 10 and further wherein said at least three ~~a plurality of~~ exposed material layers of the ONO-type memory cell stack includes:

(b.9) a second silicon nitride layer; disposed above the first silicon layer.

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Claim 12 (*Currently Amended*): The sidewall dielectric forming method of Claim **3** ~~1~~ and further wherein:

a height variation ratio, $R_H = H_{outer}/H_{inner}$, determined for the ONO-type memory cell stack after formation of the sidewall dielectric by the dry ISSG process, is about 1.20 or less, where H_{inner} represents a stack height at a lateral position in the stack that is spaced away from the stack edges and where H_{outer} represents a stack height at a lateral position near or at one of the stack edges.

Claim 13 (*Currently Amended*): The sidewall dielectric forming method of Claim **10** ~~1~~ and further wherein lateral sidewall breakdown voltages are substantially uniform along the height of the ONO-type memory cell stack after formation of the sidewall dielectric by the dry ISSG process.

Claim 14 (*Currently Amended*): The sidewall dielectric forming method of Claim **10** ~~1~~ and further wherein a larger erase speed is obtained in a memory cell having said ONO-type memory cell stack after formation of the sidewall dielectric by the dry ISSG process, where the larger erase speed is larger than a corresponding erase speed obtained in a corresponding memory cell having an ONO-type memory cell stack with sidewall dielectric formed by an HTO process.

Claim 15 (*Currently Amended*): The sidewall dielectric forming method of Claim 1 and further comprising:

(b) after said dry ISSG process, forming further and supplemental sidewall dielectric by a non-ISSG ~~sidewall dielectric forming~~ **oxidation** process.

Claims 16-20: (*Canceled*).

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Claim 21 (*New*): The sidewall dielectric forming method of Claim 1 and further comprising:

(a.1a) setting the O_2 flow rate over the range of about 3slm to about 10slm (ten standard liters per minute).

Claim 22 (*New*): The sidewall dielectric forming method of Claim 21 and further comprising:

(a.2a) setting the H_2 flow rate over the range of about 0.1slm to about 1slm.

Claim 23 (*New*): A method of forming sidewall dielectric on an ONO-type memory cell stack where at least one sidewall of the ONO-type memory cell stack includes at least three exposed material layers with at least two of the exposed material layers being respectively composed of different materials, the method comprising:

(a) subjecting the at least three exposed material layers of the sidewall of the ONO-type memory cell stack to a dry ISSG process (In-Situ Steam Generation) where the dry ISSG process generates short lived oxygen radicals whose reactivity extinguishes before the short lived oxygen radicals are able to permeate as deep into the ONO-type memory cell stack and oxidize materials therein as would the reactive oxygen of a High Temperature Oxidation (HTO) process applied to an essentially same ONO-type memory cell stack.

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